



DSS4240T

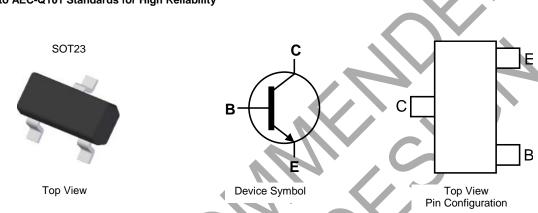
**40V NPN LOW SATURATION TRANSISTOR IN SOT23** 

#### Features

- BV<sub>CEO</sub> > 40V
- I<sub>C</sub> = 2A High Continuous Collector Current
- I<sub>CM</sub> = 3A Peak Pulse Current
- Low Saturation Voltage 180mV Max @ I<sub>C</sub> = 1A
- R<sub>CE(SAT)</sub> = 60mΩ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary PNP Type: DSS5240T
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



#### Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS4240T-7	NRND (use ZXTN4240F-7)	ZN2	7	8	3000
DSS4240T-13	NRND (use ZXTN4240F-7)	ZN2	13	8	10,000

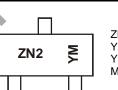
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.
- 5. NRND Not recommended for new design.

#### **Marking Information**

Notes:



ZN2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code K	еу											
Year	2013	2014	2015	2016	2017	2018	3 201	9 2	020	2021	2022	2023
Code	А	В	С	D	E	F	G		H		J	K
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Peak Pulse Collector Current	I <sub>CM</sub>	3	А
Continuous Collector Current	I <sub>C</sub>	2	А
Peak Base Current	I <sub>BM</sub>	0.3	А

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	PD	730	mW
Power Dissipation (Note 7)	PD	600	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	R <sub>ÐJA</sub>	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	R <sub>ÐJA</sub>	209	°C/W
Thermal Resistance, Junction to Lead (Note 8)	R <sub>ƏJL</sub>	75	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

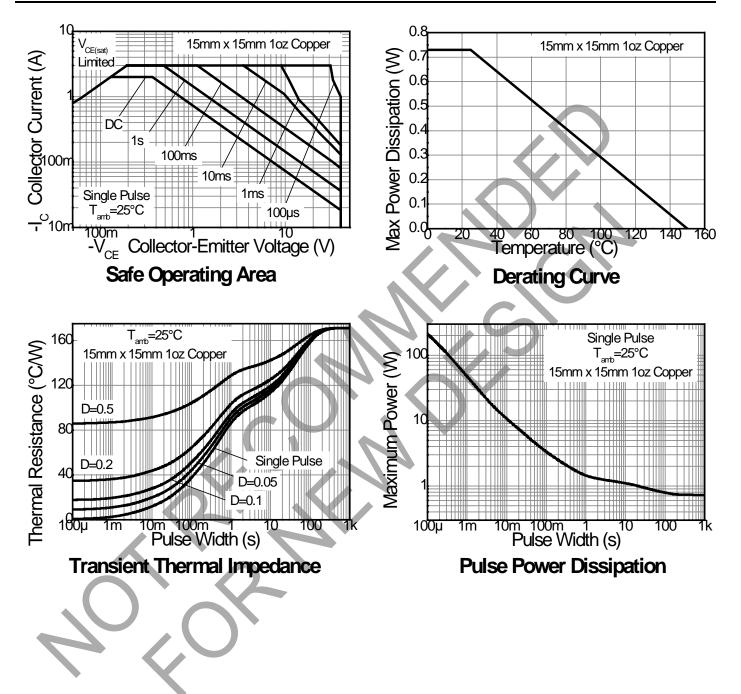
#### ESD Ratings (Note 9)

Characteristic		Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model		ESD HBM	4000	V	ЗA
Electrostatic Discharge—Machine Model		ESD MM	400	V	С

6. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Same as Note 5, except the device is mounted on minimum recommended pad layout.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115. Notes:



## Thermal Characteristics and Derating Information



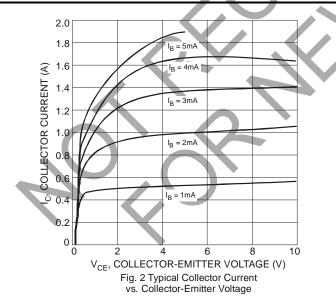


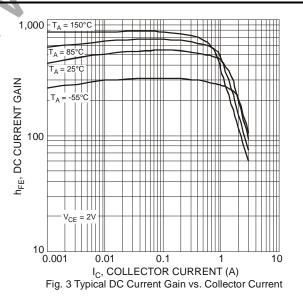
#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						·
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	40	—	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	40	—	—	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	—	—	V	I <sub>E</sub> = 100μA
Collector-Base Cutoff Current		_	—	100	nA	$V_{CB} = 30V, I_E = 0$
Collector-Base Cutori Current	I <sub>CBO</sub>	—	—	50	μA	$V_{CB} = 30V, I_E = 0, T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	I <sub>EBO</sub>	—	—	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 8)						
		350	_	—		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	L .	300	—			$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h <sub>FE</sub>	300	—	-		$V_{CE} = 2V, I_C = 1A$
		150	—			$V_{CE} = 2V, I_C = 2A$
		—	—	70	mV	I <sub>C</sub> = 100mA, I <sub>B</sub> = 1mA
		—	30	100		$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—		180		$I_{\rm C} = 750 {\rm mA}, I_{\rm B} = 15 {\rm mA}$
			/-	180		$I_{C} = 1A, I_{B} = 50mA$
		—		320		$I_{C} = 2A, I_{B} = 200 \text{mA}$
Equivalent On-Resistance	R <sub>CE(sat)</sub>	-	60	200	mΩ	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-	—	1.1	V	$I_{\rm C} = 2A, I_{\rm B} = 200 {\rm mA}$
Base-Emitter Turn-on Voltage	V <sub>BE(on)</sub>		Y	0.75	V	$V_{CE} = 2V, I_{C} = 100 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	fτ	100	—	_	MHz	$V_{CE} = 10V, I_C = 100mA, f = 100MHz$
Output Capacitance	Cob		_	20	pF	V <sub>CB</sub> = 10V, f = 1MHz

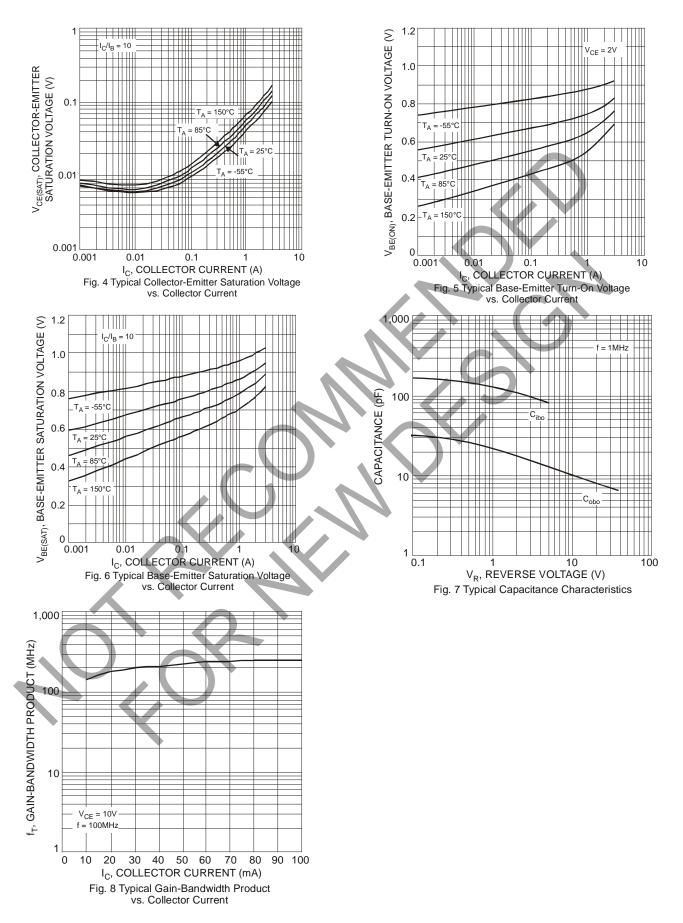
Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.

## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)





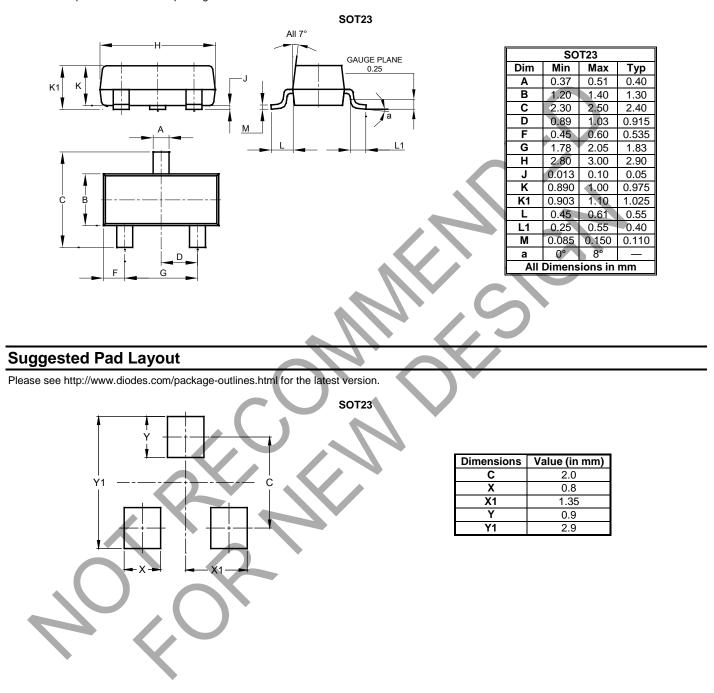






## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





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